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which leads to **threshold voltage** increase for devices close to the well edge.

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Semiconductor Manufacturing, 2005. ISSM 2005, IEEE International Symposium
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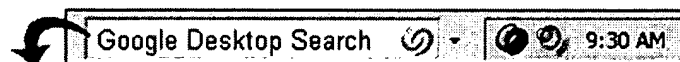
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